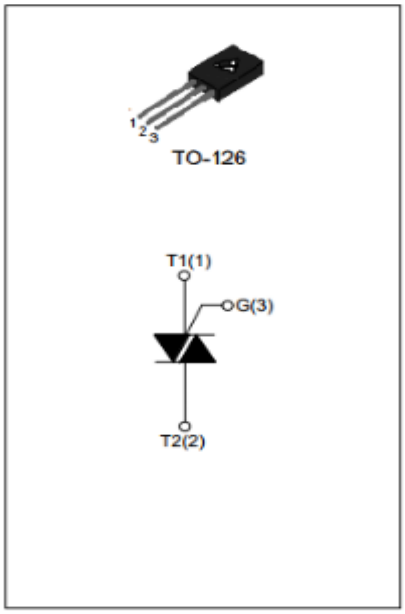
BT134 TRIACs

●Product features

Single mesa structure (Single Mesa),
Table glass passivation process,
three layers of metal on the back
The applicable model： BT134,



●The main purposes

Mahjong machine, washing machine
Solid state relay, AC motor speed control

●Package

TO-126

●Main Feature (Tj=25℃)

Symbol	Value	Unit
$I_{T(RMS)}$	4.0	A
V_{DRM} / V_{RRM}	600/800	V
V_{TM}	1.5	V

●Absolute ratings (Limiting Values)

Symbol	Parameter	Value	Unit
I_{TSM}	Non repetitive surge peak on-state Current (tp=10ms)	40	A
I^2t	(tp=10ms)	5.1	A^2S
dI/dt	I_G=2IGT，tr≤100ns,Tj=125℃	50	A/μs
I_{GM}	Peak gate current(tp=20us)	4	A
$P_{G(AV)}$	Average gate power	1	W
Tstg Tj	Storage temperature Operating junction temperature	-40--+150 -40--+125	℃

●Thermai Resistances

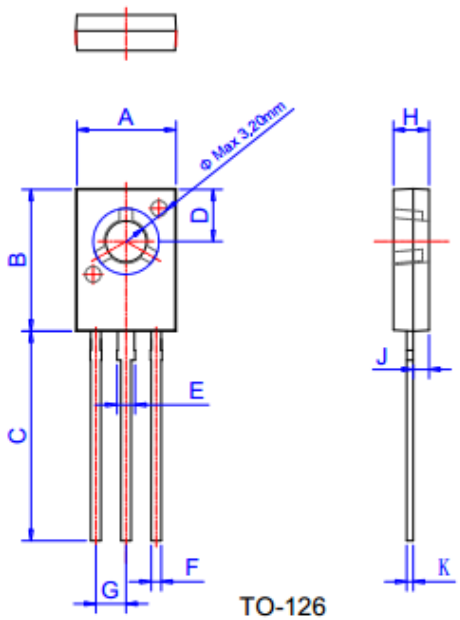
Symbol	Parameter		Value	Unit
Rth (j-c)	Junction to case	TO-126	5.4	℃/W

●Electrical characteristics (Tj=25℃ unless otherwise stated)

Symbol	Test Conditions		Value	Unit
I_{GT}	V_D=12V, R_L=30Ω	Ⅰ Ⅱ Ⅲ	<5	mA
		Ⅳ	<10	
I_{DRM}	$V_D=V_{DRM}$	T_j=25℃	≤5	μA
		T_j=125℃	≤1	mA
I_{RRM}	$V_D=V_{RRM}$	T_j=25℃	≤5	μA
		T_j=125℃	≤1	mA
I_L	I_G=1.2I_{GT}	Ⅰ Ⅲ	<25	mA
		Ⅳ	<25	
		Ⅱ	<30	
V_{GT}	V_D=12V, R_L=30Ω		≤1.3	V
V_{GD}	$V_D=V_{DRM}$, R_L=3.3KΩ Tj=125℃		≥0.2	V
V_{TM}	I_{TM}=6A,tp=380μs		1.6	V
I_H	V_D=12V， I_T=200mA		≤10 ≤15 ≤35 ≤60 ≤10 ≤15	mA
dV/dt	V_D=67%V_{DRM}, GateOpen, Tj=125℃		≥20 ≥40 ≥200 ≥800 ≥20 ≥50	v/μs

●Measure of package

TO-126



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	7.40		7.80	0.291		0.307
B	10.6		11.2	0.417		0.441
C	15.3		16.3	0.602		0.642
D	3.90		4.10	0.154		0.161
E	1.17		1.47	0.046		0.058
F	0.66		0.86	0.026		0.034
G		2.29			0.090	
H	2.50		2.90	0.098		0.114
J	1.10		1.50	0.043		0.059
K	0.45		0.60	0.018		0.024

FIG.1 Maximum power dissipation versus RMS on-state current

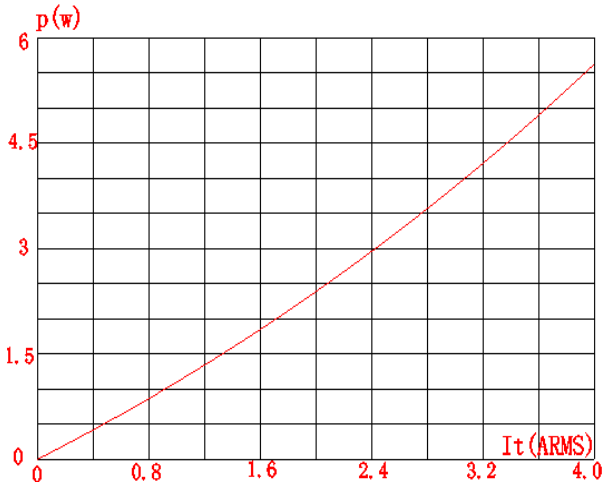


FIG.2: RMS on-state current versus case temperature

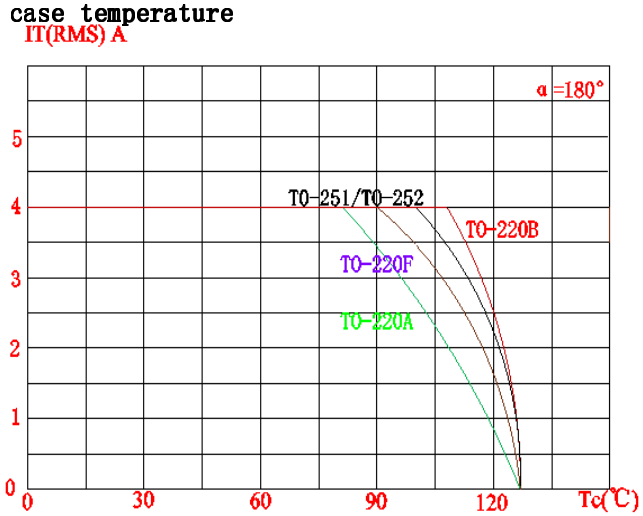


FIG.3: Surge peak on-state current versus number of cycles

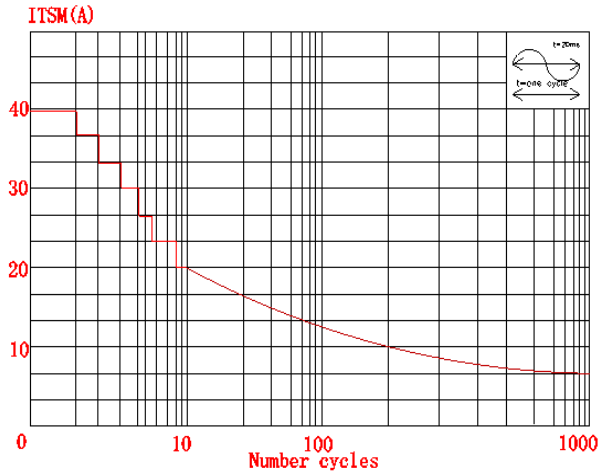


FIG.4: On-state characteristics (maximum values)

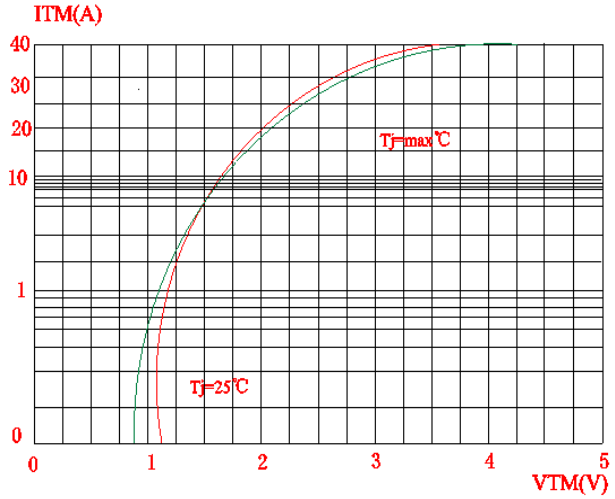


FIG.5: Non-repetitive surge peak on-state currentfor a sinusoidal pulse with width tp<20ms, and corresponding value of I^2t (dI/dt < 50A/μs)

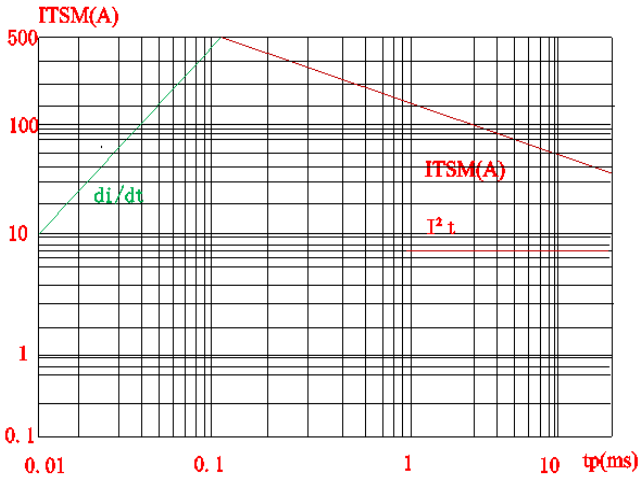


FIG.6: Relative variations of gate trigger current holding current and latching current versus junction temperature